

## Silicon NPN Power Transistors

## BD233 BD235 BD237

## DESCRIPTION

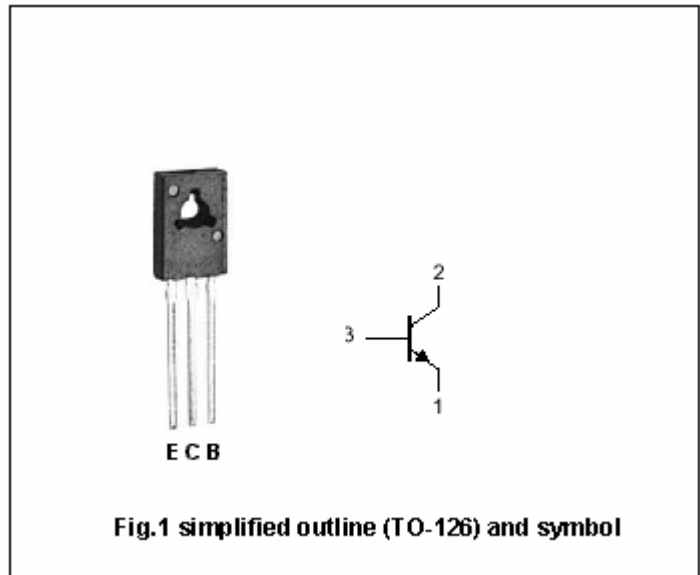
- With TO-126 package
- Complement to type BD234 /236 /238

## APPLICATIONS

- For medium power linear and switching applications

## PINNING

PIN	DESCRIPTION
1	Emitter
2	Collector;connected to mounting base
3	Base



## Absolute maximum ratings (Ta=25°C)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V <sub>CBO</sub>	Collector-base voltage	BD233	45	V
		BD235	60	
		BD237	100	
V <sub>CEO</sub>	Collector-emitter voltage	BD233	45	V
		BD235	60	
		BD237	80	
V <sub>EBO</sub>	Emitter -base voltage	Open collector	5	V
I <sub>C</sub>	Collector current (DC)		2	A
I <sub>CM</sub>	Collector current-Peak		6	A
P <sub>C</sub>	Collector power dissipation	T <sub>C</sub> =25°C	25	W
T <sub>j</sub>	Junction temperature		150	°C
T <sub>stg</sub>	Storage temperature		-65~150	°C

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## CHARACTERISTICS

T<sub>j</sub>=25°C unless otherwise specified

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SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT	
V <sub>CEsat</sub>	Collector-emitter saturation voltage	I <sub>C</sub> =1A; I <sub>B</sub> =0.1A			0.6	V	
V <sub>BE</sub>	Base-emitter on voltage	I <sub>C</sub> =1A; V <sub>CE</sub> =2V			1.3	V	
V <sub>CEO(SUS)</sub>	Collector-emitter sustaining voltage	BD233	I <sub>C</sub> =0.1A; I <sub>B</sub> =0	45		V	
		BD235		60			
		BD237		80			
I <sub>CBO</sub>	Collector cut-off current	BD233			100	μA	
		BD235					V <sub>CB</sub> =60V; I <sub>E</sub> =0
		BD237					V <sub>CB</sub> =100V; I <sub>E</sub> =0
I <sub>EBO</sub>	Emitter cut-off current	V <sub>EB</sub> =5V; I <sub>C</sub> =0			1	mA	
h <sub>FE-1</sub>	DC current gain	I <sub>C</sub> =150mA; V <sub>CE</sub> =2V	40				
h <sub>FE-2</sub>	DC current gain	I <sub>C</sub> =1A; V <sub>CE</sub> =2V	25				
f <sub>T</sub>	Transition frequency	I <sub>C</sub> =250mA; V <sub>CE</sub> =10V	3			MHz	

PACKAGE OUTLINE

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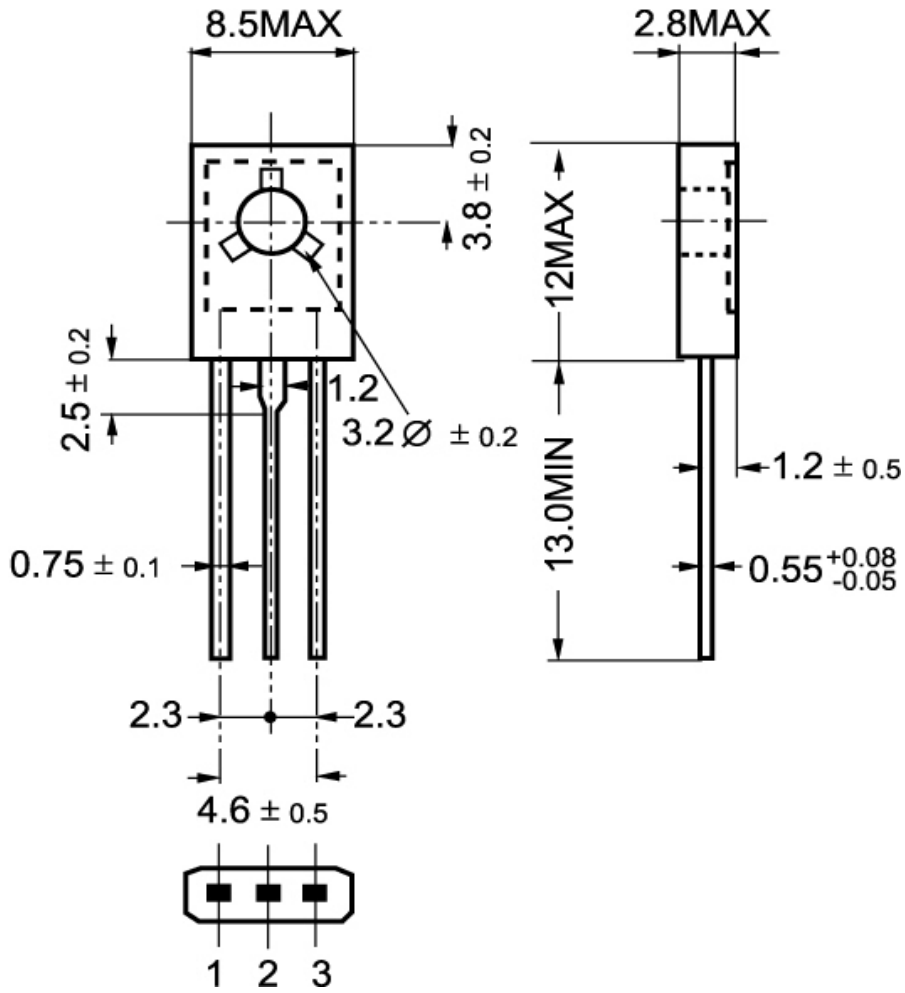


Fig.2 Outline dimensions